Performance Characteristics:

- Frequency band: DC~40GHz
- Insertion loss: 1.4dB
- Isolation: 33dB
- Input/output voltage standing wave ratio: 1.2/1.2
- Control voltage: 0/-5V
- Chip size: 1.1mm×0.75mm×0.1mm

Product Description:

CW-SW10040 is a GaAs MMIC reflective single-pole single-throw switch chip with frequency range covering D C~40GHz, entire band insertion loss less than 1.4dB and isolation greater than 33dB.The CW-SW10040 is powered by 0/-5V.

Electrical parameters: (T_A=25°C, Vs=0/-5V)

Indicators	Minimum	Typical value	Maximum value	Units
Frequency range	DC~40			GHz
Insertion loss	-	-	1.4	dB
isolation	33	-	-	dB
Input voltage standing wave	-	-	1.2	-
Output voltage standing wave	-	-	1.2	-

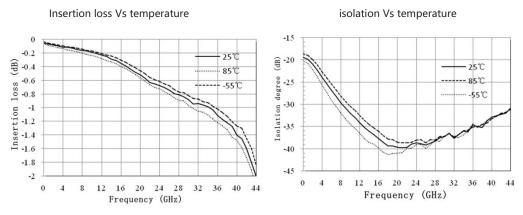
Use limit parameters: (Exceeding any of the above maximum limits risks permanent damage.)

Input power	+30dBm
Control voltage	-8~+1V
Storage temperature	-65℃~150℃
OService temperature	-55℃~125℃

Switch truth table:

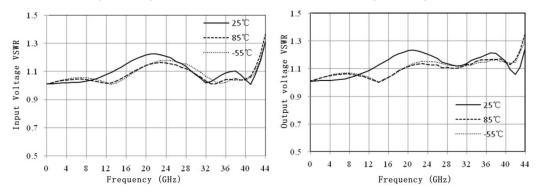
Control voltage (V)	On-off state
VS	IN-OUT
0	OFF
-5	ON

Typical curves:

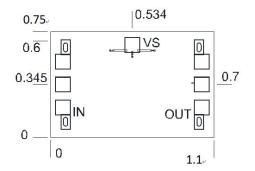


Open-state input voltage standing wave ratio Vs temperature

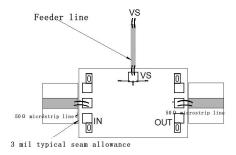
output voltage standing wave ratio Vs temperature







Suggested assembly drawing:



Instructions:

Note: I/O no straight capacitance

Storage: The chip must be placed in a container with electrostatic protection and stored in a nitrogen environment. **Cleaning treatment:** The bare chip must be operated and used in a purified environment. It is forbidden to use liquid cleaning agent to clean the chip.

Electrostatic protection: Strictly comply with the ESD protection requirements to avoid electrostatic damage to the components.

General operation: Use vacuum chuck or precision pointed tweezers to pick up the chip. Avoid touching the surface of the chip with tools or fingers during handling.

Mounting operation: The chip can be installed using AuSn solder eutectic welding or conductive adhesive bonding process. The mounting surface must be clean and flat.

Bonding operation: Input and output with 2 (recommended diameter of 25um gold wire) bonding wire, bonding wire length less than 250um is optimal. It is recommended to use the smallest possible ultrasonic energy. Bonding begins at the pressure point on the chip and ends at the package (or substrate).